

## Silicon NPN Power Transistors

2SC4927

## DESCRIPTION

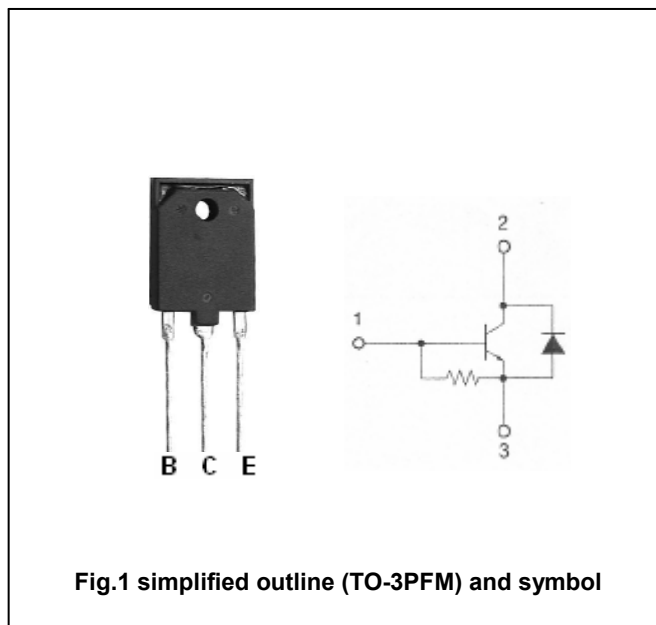
- With TO-3PFM package
- Built-in damper diode
- High breakdown voltage

## APPLICATIONS

- TV/Character display horizontal deflection output applications

## PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | Base        |
| 2   | Collector   |
| 3   | Emitter     |

Absolute maximum ratings( $T_a = \square$ )

| SYMBOL         | PARAMETER                    | CONDITIONS        | VALUE   | UNIT      |
|----------------|------------------------------|-------------------|---------|-----------|
| $V_{CEO}$      | Collector-emitter voltage    | Open base         | 1500    | V         |
| $V_{EBO}$      | Emitter-base voltage         | Open collector    | 6       | V         |
| $I_C$          | Collector current            |                   | 8       | A         |
| $I_{C(peak)}$  | Collector current-peak       |                   | 9       | A         |
| $I_{C(surge)}$ | Collector current-surge      |                   | 18      | A         |
| $I_o$          | C to E diode forward current |                   | 8       | A         |
| $P_C$          | Collector power dissipation  | $T_C = 25\square$ | 50      | W         |
| $T_j$          | Junction temperature         |                   | 150     | $\square$ |
| $T_{stg}$      | Storage temperature          |                   | -55~150 | $\square$ |

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## CHARACTERISTICS

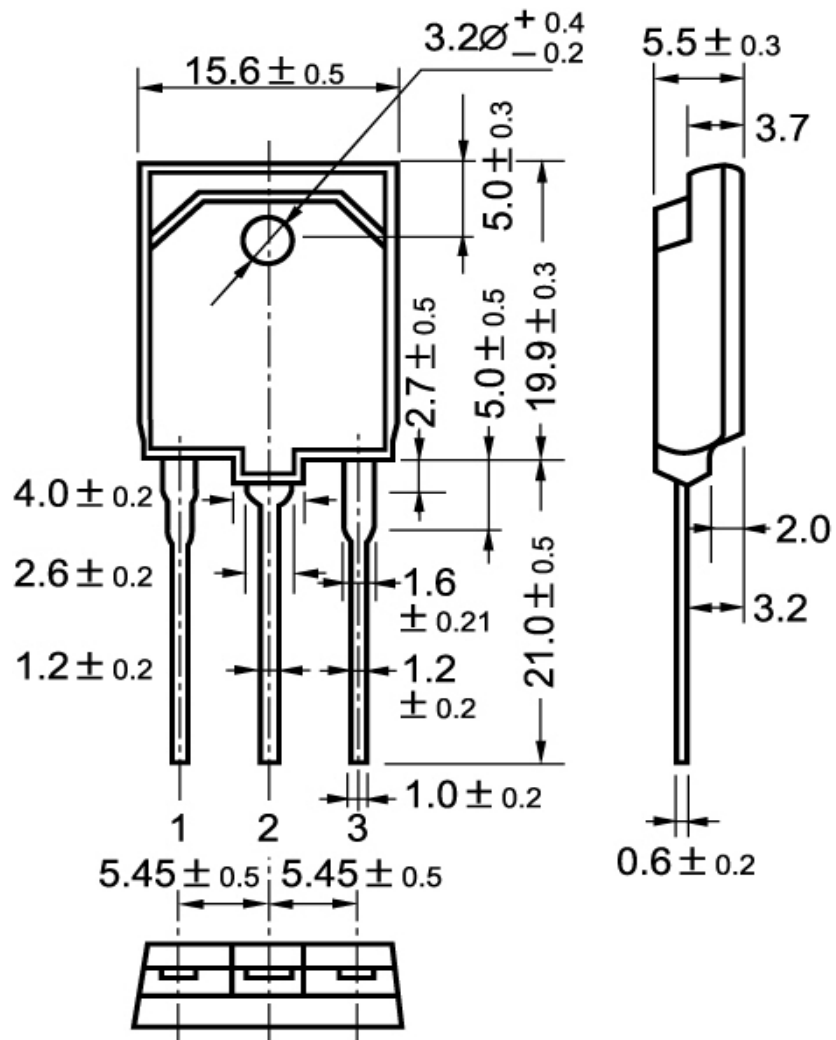
T<sub>j</sub>=25°C unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS                                                                                    | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|-----------------------------------------------------------------------------------------------|-----|------|-----|------|
| V <sub>(BR)EBO</sub> | Emitter-base breakdown voltage       | I <sub>E</sub> =500mA ; I <sub>C</sub> =0                                                     | 6   |      |     | V    |
| I <sub>CES</sub>     | Collector cut-off current            | V <sub>CE</sub> =1500V; R <sub>BE</sub> =0                                                    |     |      | 0.5 | mA   |
| h <sub>FE</sub>      | DC current gain                      | I <sub>C</sub> =1A ; V <sub>CE</sub> =5V                                                      |     |      | 25  |      |
| V <sub>CE(sat)</sub> | Collector-emitter saturation voltage | I <sub>C</sub> =6A ; I <sub>B</sub> =1.2A                                                     |     |      | 5   | V    |
| V <sub>BE(sat)</sub> | Base-emitter saturation voltage      | I <sub>C</sub> =6A ; I <sub>B</sub> =1.2A                                                     |     |      | 1.5 | V    |
| V <sub>ECF</sub>     | Diode forward voltage                | I <sub>F</sub> =8A                                                                            |     |      | 2.0 | V    |
| t <sub>f</sub>       | Fall time                            | I <sub>CP</sub> =6A; f <sub>H</sub> =31.5kHz<br>I <sub>B1</sub> =1.2A; I <sub>B2</sub> =-2.4A |     |      | 0.5 | μs   |

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## PACKAGE OUTLINE



### Fig.2 outline dimensions

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